J105/106/107

N-Channel JFETs

Product Summary

Part Number	$V_{GS(off)}$ (V)	$r_{DS(on)}$ Max (Ω)	$I_{D(off)}$ Typ (pA)	t_{ON} Typ (ns)
J105	−4.5 to −10	3	10	14
J106	−2 to −6	6	10	14
J107	−0.5 to −4.5	8	10	14

Features

- Low On-Resistance: J105 < 3 Ω
- Fast Switching—t_{ON}: 14 ns
- Low Leakage: 10 pA
- Low Capacitance: 20 pF
- Low Insertion Loss

Benefits

- Low Error Voltage
- High-Speed Analog Circuit Performance
- Negligible "Off-Error," Excellent Accuracy
- Good Frequency Response
- Eliminates Additional Buffering

Applications

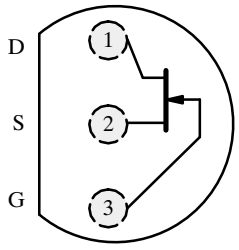
- Analog Switches
- Choppers
- Sample-and-Hold
- Normally "On" Switches
- Current Limiters

Description

The J105/106/107 are high-performance JFET analog switches designed to offer low on-resistance and fast switching. $r_{DS(on)}$ <3 Ω is guaranteed for the J105 making this device the lowest of any commercially available JFET.

The low cost TO-226AA (TO-92) plastic package is available in a wide range of tape-and-reel options (see Packaging Information). For similar products in TO-206AC (TO-52) packaging, see the U290/291 data sheet.

TO-226AA
(TO-92)



Top View

Absolute Maximum Ratings

Gate-Drain, Gate-Source Voltage . . . . . −25 V
Gate Current . . . . . 50 mA
Storage Temperature . . . . . −55 to 150°C
Operating Junction Temperature . . . . . −55 to 150°C

Power Dissipation[a] . . . . . 350 mW

Notes
a. Derate 2.8 mW/°C above 25°C

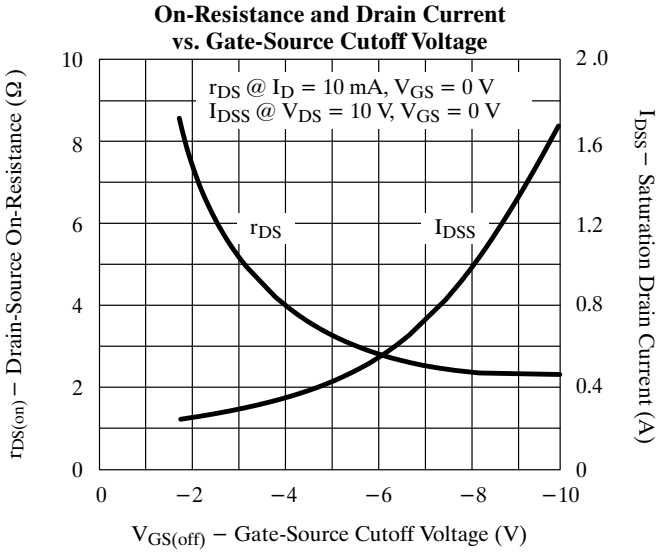
J105/106/107

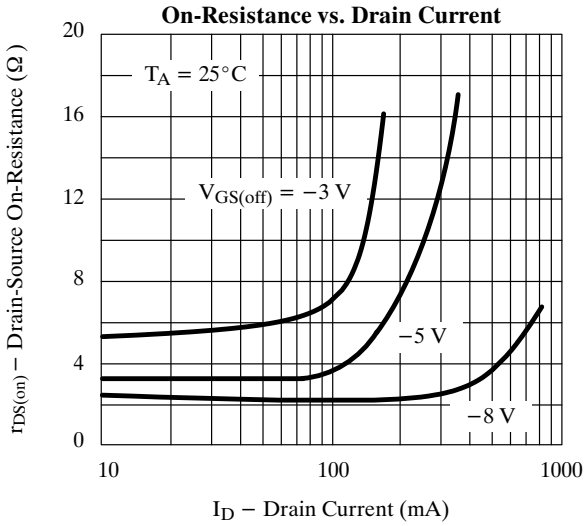
Specifications[a]

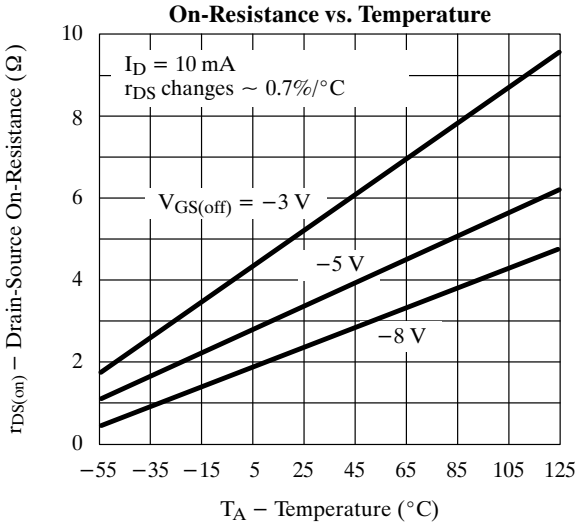
Parameter	Symbol	Test Conditions	Typ[b]	Limits J105 Min	Limits J105 Max	Limits J106 Min	Limits J106 Max	Limits J107 Min	Limits J107 Max	Unit
Static										
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = -1$ µA , $V_{DS} = 0$ V	−35	−25		−25		−25		V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 5$ V, $I_D = 1$ µA		−4.5	−10	−2	−6	−0.5	−4.5	
Saturation Drain Current[c]	I_{DSS}	$V_{DS} = 15$ V, $V_{GS} = 0$ V		500		200		100		mA
Gate Reverse Current	I_{GSS}	$V_{GS} = -15$ V, $V_{DS} = 0$ V	−0.02		−3		−3		−3	nA
		$T_A = 125°C$	−10							
Gate Operating Current[c]	I_G	$V_{DG} = 10$ V, $I_D = 25$ mA	−0.01							
Drain Cutoff Current	$I_{D(off)}$	$V_{DS} = 5$ V, $V_{GS} = -10$ V	0.01		3		3		3	
		$T_A = 125°C$	5							
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 0$ V, $I_D = 1$ mA			3		6		8	Ω
Gate-Source Forward Voltage	$V_{GS(F)}$	$I_G = 1$ mA , $V_{DS} = 0$ V	0.7							V
Dynamic										
Common-Source Forward Transconductance[c]	g_{fs}	$V_{DS} = 10$ V, $I_D = 25$ mA f = 1 kHz	55							mS
Common-Source Output Conductance[c]	g_{os}		5							
Drain-Source On-Resistance	$r_{ds(on)}$	$V_{GS} = 0$ V, $I_D = 0$ mA , f = 1 kHz			3		6		8	Ω
Common-Source Input Capacitance	C_{iss}	$V_{DS} = 0$ V, $V_{GS} = 0$ V, f = 1 MHz	120		160		160		160	pF
Common-Source Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 0$ V, $V_{GS} = -10$ V f = 1 MHz	20		35		35		35	
Equivalent Input Noise Voltage	$\overline{e}_n$	$V_{DG} = 10$ V, $I_D = 25$ mA f = 1 kHz	3							$\frac{nV}{\sqrt{Hz}}$
Switching										
Turn-On Time	$t_{d(on)}$	$V_{DD} = 1.5$ V, $V_{GS(H)} = 0$ V See Switching Diagram	6							ns
	t_r		8							
Turn-Off Time	$t_{d(off)}$		5							
	t_f		9							

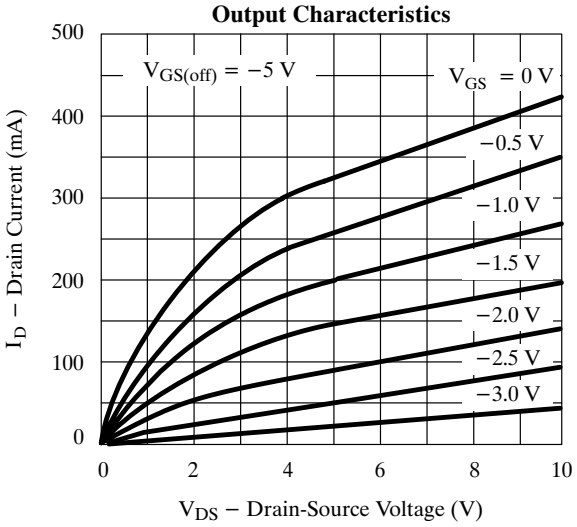
Notes
a. $T_A = 25°C$ unless otherwise noted. NVA
b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
c. Pulse test: PW ≤ 300 µs duty cycle ≤ 3%.

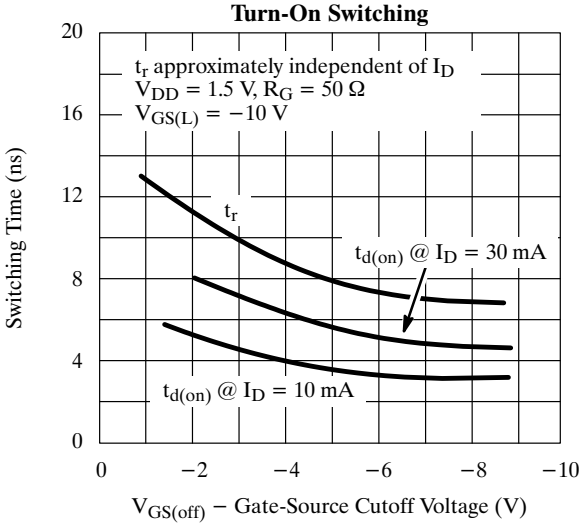
Typical Characteristics

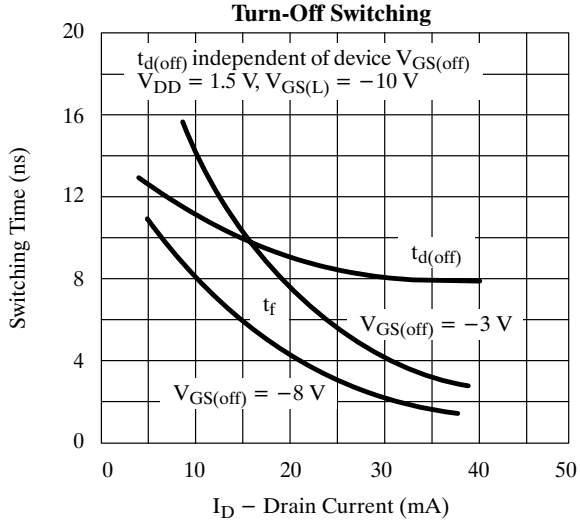








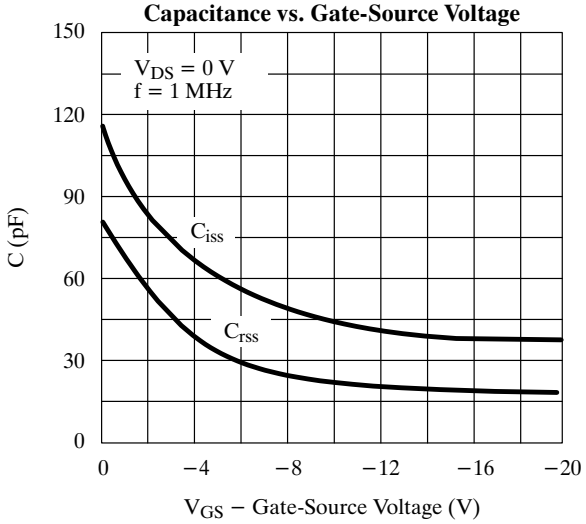




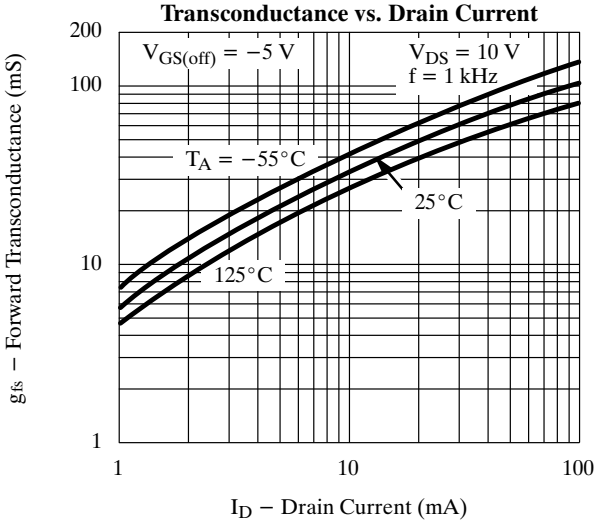
J105/106/107

Typical Characteristics (Cont'd)

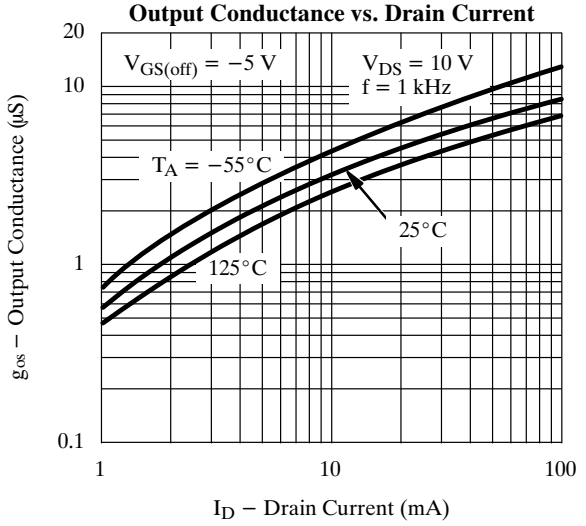
Capacitance vs. Gate-Source Voltage



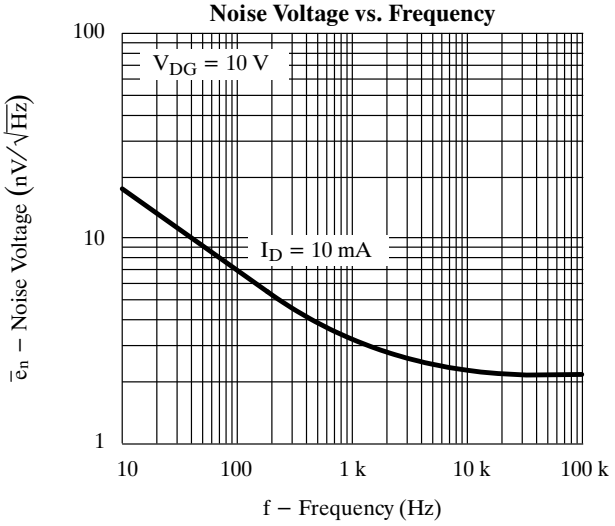
Transconductance vs. Drain Current



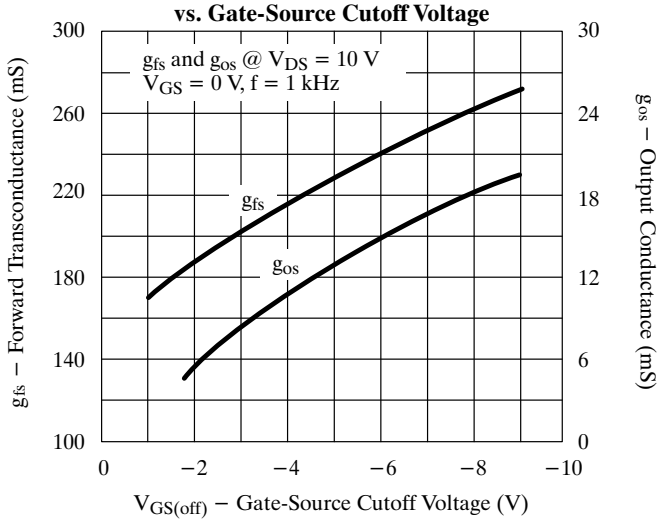
Output Conductance vs. Drain Current



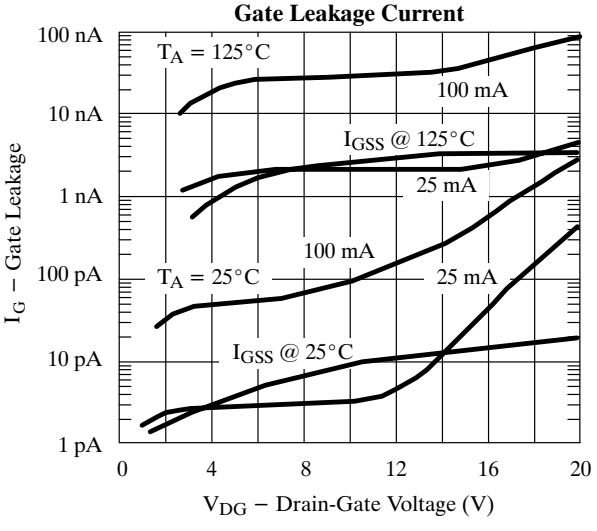
Noise Voltage vs. Frequency



Forward Transconductance and Output Conductance vs. Gate-Source Cutoff Voltage



Gate Leakage Current



Switching Time Test Circuit

	J105	J106	J107
$V_{GS(L)}$	−12V	−7V	−5V
R_L	50 Ω	50 Ω	50 Ω
$I_{D(on)}$	28 mA	27 mA	26 mA

*Non-inductive

Input Pulse

Rise Time < 1 ns
Fall Time < 1 ns
Pulse Width 100 ns
PRF 1 MHz

Sampling Scope

Rise Time 0.4 ns
Input Resistance 10 MΩ
Input Capacitance 1.5 pF